

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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OPB710, OPB710F, OPB730, OPB730F



Features:

- Choice of phototransistor or photodarlington output
- · Unfocused for sensing diffuse surface
- Mounted on standard TO-72 header
- Available in clear encapsulating epoxy (OPB710, OPB730)
- Filtered to reduce the effect of visible or fluorescent light (OPB710F, OPB730F)



Description:

OPB710 and **OPB710F** consist of a gallium arsenide infrared emitting diode and an NPN silicon phototransistor. **OPB730** and **OPB730F** consist of a gallium arsenide infrared emitting diode and an NPN silicon photodarlington.

On each sensor, the emitting diode and detector are mounted side-by-side on parallel axes in a standard TO-72 header. A black plastic sleeve is attached and filled with encapsulating epoxy to cover the emitter and detector.

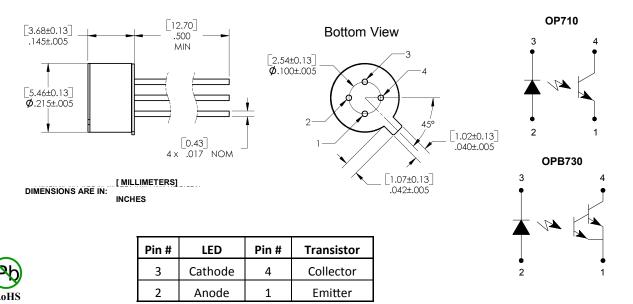
The **OPB710F** and **OPB730F** ("F" versions) have a filtering material added to the epoxy to reduce the effect of ambient light. The package contains an internal barrier which prevents diode emissions from reaching the sensor directly.

Custom electrical, wire and cabling and connectors are available. Contact your local representative or OPTEK for more information.

Applications:

- Non-contact reflective object sensor
- Assembly line automation
- Machine automation
- Machine safety
- End of travel sensor
- Door sensor

Part Number	LED Peak Wavelength	Sensor	Reflection Distance	
OPB710		Transistor		
OPB710F	025 nm		0.350" (6.35~~)	
OPB730	935 nm	Darlington	0.250" (6.35mm)	
OPB730F		Darinigton		





OPB710, OPB710F, OPB730, OPB730F



Maximum Ratings (T _A = 25° C unless	s otherwi	se note	۰d)					
			u,					
Storage Temperature Range								
Operating Temperature Range								
Lead Soldering Temperature [1/16 inch (1.6mm) from the case for 5 sec. with soldering iron] ⁽¹⁾								
Forward DC Current								
Peak Forward Current (1 μs pulse width, 300 pps)								
Reverse DC Voltage								
Power Dissipation ⁽²⁾								
tosensor						1		
Collector-Emitter Voltage OPB710, OPB710F OPB730, OPB730F								
Emitter-Collector Voltage								
Collector DC Current								
Power Dissipation ⁽³⁾								
Characteristics (T_A = 25° C unless otherwise)	nerwise n	oted)						
PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS			
Input Diode (see OP165W for additional information)								
Forward Voltage	-	-	1.5	V	I _F = 50 mA			
Reverse Current	-	-	100	μΑ	V _R = 3 V			
Output Phototransistor (See OP505W for additional information)								
Collector-Emitter Breakdown Voltage	30	-	-	V	I _C = 1 mA			
Emitter-Collector Breakdown Voltage	5	-	-	V	Ι _Ε = 100 μΑ			
Collector Dark Current OPB710, OPB710F OPB730, OPB730F		- -	100 250	nA	$V_{CE} = 5 \text{ V}, I_F = 0, E_E \le 0.1 \mu\text{W/cm}^2$			
Crosstalk ⁽⁵⁾ OPB710, OPB710F OPB730, OPB730F			100 500	nA	$I_F = 50 \text{ mA}$, $V_{CE} = 5 \text{ V (no reflecting surface)}$			
On-State Collector Current ⁽⁴⁾ OPB710, OPB710F OPB730, OPB730F	150 1	-	-	μA mA	I _F = 50 mA, V _{CE} = 5 V, d = 0.250" (6.35 mm)			
	oldering Temperature [1/16 inch (1.6mm) from the properties of DC Current (1 μs pulse width, 300 pps) and DC Voltage Dissipation (2) cosensor cor-Emitter Voltage OPB710, OPB710F OPB730, OPB730F Collector Voltage cor DC Current Dissipation (3) Characteristics (T _A = 25° C unless other PARAMETER (see OP165W for additional information) Forward Voltage Reverse Current cotransistor (See OP505W for additional information) Collector-Emitter Breakdown Voltage Emitter-Collector Breakdown Voltage Collector Dark Current OPB710, OPB710F OPB730, OPB710F OPB730, OPB710F OPB730, OPB710F OPB730, OPB710F OPB730, OPB710F OPB730, OPB710F OPB710, OPB710F OPB710F OPB710, OPB710F OPB710, OPB710F OPB710F OPB710, OPB710F O	d DC Current orward Current (1 μs pulse width, 300 pps) DC Voltage Dissipation ⁽²⁾ cosensor or-Emitter Voltage OPB710, OPB710F OPB730, OPB730F -Collector Voltage or DC Current Dissipation ⁽³⁾ Characteristics (T _A = 25° C unless otherwise r PARAMETER MIN (see OP165W for additional information) Forward Voltage Reverse Current cotransistor (See OP505W for additional information) Collector-Emitter Breakdown Voltage 5 Collector Dark Current OPB710, OPB710F OPB730, OPB710F OPB730, OPB710F OPB730, OPB730F - On-State Collector Current ⁽⁴⁾ OPB710, OPB710F OPB730, OPB710F OPB710, OPB710F OPB730, OPB710F OPB710, OPB710F	d DC Current orward Current (1 µs pulse width, 300 pps) DC Voltage Dissipation (2) OPB710, OPB710F OPBRAMETER Reverse Current Cotlector-Emitter Breakdown Voltage Emitter-Collector Breakdown Voltage Emitter-Collector Breakdown Voltage Collector Dark Current OPB710, OPB730F Collector Dark Current OPB710, OPB730F Collector Softman (3) Collector Softman (4) Collector Softman (5) Collector Softman (5) Collector Softman (5) Collector Softman (6) Emitter-Collector Breakdown Voltage Collector Dark Current OPB710, OPB730F OPB730, OPB730F OPB730, OPB730F OPB730, OPB730F OPB730, OPB730F OPB730, OPB730F OPB710, OPB710F OPB710, OPB710F OPB730, OPB730F OPB730, OPB730F OPB730, OPB730F OPB730, OPB730F OPB730, OPB730F	d DC Current The proper state of the proper	Indering Temperature [1/16 inch (1.6mm) from the case for 5 sec. with soldering in a d DC Current by the current (1 μs pulse width, 300 pps) and DC Current by the current (1 μs pulse width, 300 pps) are DC Voltage Dissipation (2) DOF Temitter Voltage OPB710, OPB710F OPB730, OPB730 PPS AND TEMESTATION OPB710 PPS AND TEMESTATION OPB710 PPS AND TEMESTATION OPB730 PPS AND TEMESTATION OPB730 PPS AND TEMESTATION OPB730 PPS AND TEMESTATION OPB730, OPB730F AND TEMESTATION OP	Continue Continue		

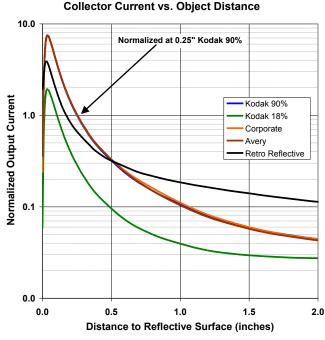
Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) Derate linearly 1.67 mW/°C above 25 °C.
- (3) Derate linearly 3.33 mW/°C above 25 ° C.
- (4) Measured using Eastman Kodak neutral white test card having 90% diffuse reflectance located .250 inch (6.35 mm) from the face of the OPB710/OPB730. Reference: Eastman Kodak, Catalog #E 152 7795.
- (5) Crosstalk (ICX) is the collector current measured with the indicated current on the input diode and with no reflecting surface. Ambient light is excluded with a black box.

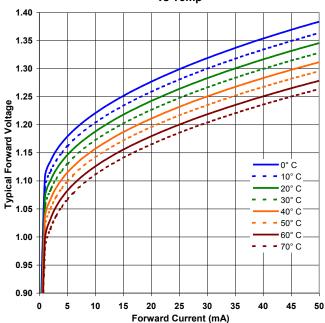
OPB710, OPB710F, OPB730, OPB730F



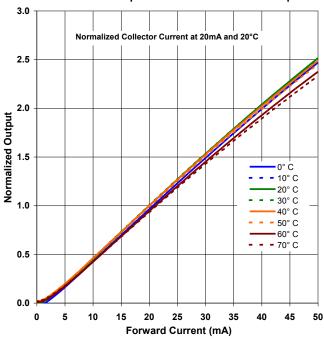
OPB710 - Normalized Collector Current vs. Object Distance



OPB710 - Forward Voltage vs Forward Current vs Temp



OPB710 - Output vs Forward Current vs Temp



OPB710, OPB710F, OPB730, OPB730F



OPB730 - Normalized
Collector Current vs. Object Distance

Normalized at 0.25" Kodak 90%

Kodak 18%

Corporate

Avery

Retro Reflective

Distance to Reflective Surface (inches)

